

# **Product Datasheet**

# Graphenea Monolayer Graphene film on 300 nm Si/SiO2

# Graphene Film

Growth Method	CVD synthesis
Transfer Method	Clean transfer method
Quality Control	Optical Microscopy & Raman checked
Appearance (Color)	Transparent
Transparency	>97%
Appearance (Form)	Film
Coverage	>95%
Number of graphene layers	1
Thickness (theoretical)	0.345 nm
AFM Thickness (air @RT)	<1nm
Electron Mobility on SiO <sub>2</sub> /Si	≈1500 cm2/V·s
Sheet Resistance on SiO <sub>2</sub> /Si (Van der Pauw)	450±40 Ohms/sq. (1cm x 1cm)
Grain size	Up to 20 μm

### Substrate

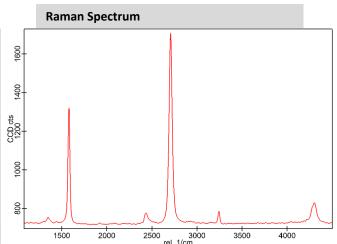
### SiO<sub>2</sub>/Si

Type/Dopant	P/Bor
Orientation	<100>
Growth Method	CZ
Resistivity	1-10 ohm·cm
Thickness	525 +/- 20 μm
Front Surface	polished
Flats	2 SEMI
Coating	300 nm thermal oxide on one side
Dielectric Constant of the SiO2 layer	3.9

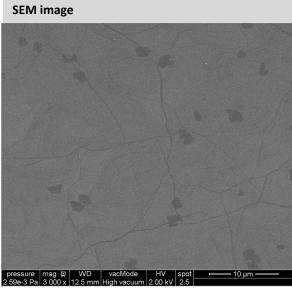


# Optical Microscopy

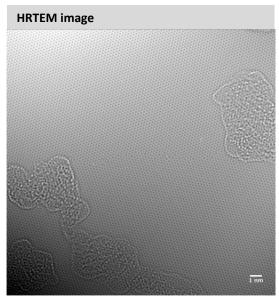
Monolayer Graphene on 300nm SiO<sub>2</sub>/Si



- Monolayer Graphene on 90nm SiO2/Si
- Measured with 453nm laser wavelength on a substrate with
- 1-100 Ohm cm resistivity
- I(G)/I(2D)<1
- I(D)/I(G)<0.1



Monolayer Graphene on 300nm SiO<sub>2</sub>/Si



Suspended graphene on TEM grids